# **DRA4143T**

# Silicon PNP epitaxial planar type

For digital circuits

Complementary to DRC4143T

DRA2143T in NS through hole type package

#### ■ Features

- $\bullet$  High forward current transfer ratio  $h_{FE}$  with excellent linearity
- ullet Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Contributes to miniaturization of sets, mount area reduction
- Eco-friendly Halogen-free package

### ■ Packaging

DRA4143T0A Radial type: 5000 pcs / carton

## ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-50	V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-50	V
Collector current	$I_{\rm C}$	-100	mA
Total power dissipation	P <sub>T</sub>	300	mW
Junction temperature	Tj	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

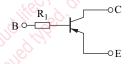
### ■ Package

Code

NS-B2-B-B

Package dimension clicks here.→

- Pin Name
  - 1: Emitter
  - 2: Collector
  - 3: Base
- Marking Symbol: LA
- Internal Connection



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Resistance value	R <sub>1</sub>	4.7	kΩ

#### ■ Electrical Characteristics $T_a = 25$ °C±3°C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_{\rm C} = -10  \mu \text{A}, I_{\rm E} = 0$	-50			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = -2 \text{ mA}, I_B = 0$	-50			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = -50 \text{ V}, I_E = 0$			-0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = -50 \text{ V}, I_{B} = 0$			-0.5	μΑ
Emitter-base cutoff current (Collector open)	$I_{\mathrm{EBO}}$	$V_{EB} = -6 \text{ V}, I_C = 0$			-0.01	mA
Forward current transfer ratio	$h_{FE}$	$V_{CE} = -10 \text{ V}, I_{C} = -5 \text{ mA}$	160		460	_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = -10 \text{ mA}, I_B = -0.5 \text{ mA}$			-0.25	V
Input voltage (ON)	V <sub>I(on)</sub>	$V_{CE} = -0.2 \text{ V}, I_{C} = -5 \text{ mA}$	-1.0			V
Input voltage (OFF)	V <sub>I(off)</sub>	$V_{CE} = -5 \text{ V}, I_{C} = -100  \mu\text{A}$			-0.4	V
Input resistance	$R_1$		-30%	4.7	+30%	kΩ

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

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